

1 Ω Typical On Resistance, ± 5 V, +12 V, +5 V, and +3.3 V, 4:1 Multiplexer

ADG1604

FEATURES

1 Ω typical on resistance
0.2 Ω on resistance flatness
±3.3 V to ±8 V dual-supply operation
3.3 V to 16 V single-supply operation
No V_L supply required
3 V logic-compatible inputs
Rail-to-rail operation
Continuous current per channel
LECSP package: 504 mA

LFCSP package: 504 mA TSSOP package: 315 mA

14-lead TSSOP and 16-lead, 4 mm × 4 mm LFCSP

APPLICATIONS

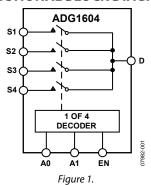
Communication systems
Medical systems
Audio signal routing
Video signal routing
Automatic test equipment
Data acquisition systems
Battery-powered systems
Sample-and-hold systems
Relay replacements

GENERAL DESCRIPTION

The ADG1604 is a complementary metal-oxide semiconductor (CMOS) analog multiplexer and switches one of four inputs to a common output, D, as determined by the 3-bit binary address lines, A0, A1, and EN. Logic 0 on the EN pin disables the device. Each switch conducts equally well in both directions when on and has an input signal range that extends to the supplies. In the off condition, signal levels up to the supplies are blocked. All switches exhibit break-before-make switching action. Inherent in the design is low charge injection for minimum transients when switching the digital inputs.

The ultralow on resistance of these switches make them ideal solutions for data acquisition and gain switching applications where low on resistance and distortion is critical. The on resistance profile is very flat over the full analog input range, ensuring excellent linearity and low distortion when switching audio signals.

FUNCTIONAL BLOCK DIAGRAM



The CMOS construction ensures ultralow power dissipation, making the parts ideally suited for portable and battery-powered instruments.

PRODUCT HIGHLIGHTS

- 1. 1.6Ω maximum on resistance over temperature.
- 2. Minimum distortion: THD + N = 0.007%.
- 3. 3 V logic-compatible digital inputs: $V_{INH} = 2.0 \text{ V}$, $V_{INL} = 0.8 \text{ V}$.
- 4. No V_L logic power supply required.
- 5. Ultralow power dissipation: <16 nW.
- 6. 14-lead TSSOP and 16-lead, 4 mm × 4 mm LFCSP.

TABLE OF CONTENTS

Features	1
Applications	
Functional Block Diagram	l
General Description	1
Product Highlights	1
Revision History	2
Specifications	3
±5 V Dual Supply	3
12 V Single Supply	4
5 V Single Supply	5
3.3 V Single Supply	6

Continuous Current per Channel, S or D
Absolute Maximum Ratings
ESD Caution8
Pin Configurations and Function Descriptions9
Typical Performance Characteristics
Test Circuits
Terminology
Outline Dimensions
Ordering Guide

REVISION HISTORY

9/09—Rev. 0 to Rev. A

1/09—Revision 0: Initial Version

SPECIFICATIONS

±5 V DUAL SUPPLY

 V_{DD} = +5 V \pm 10%, V_{SS} = -5 V \pm 10%, GND = 0 V, unless otherwise noted.

Table 1.

Parameter	25°C	–40°C to +85°C	–40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			V_{DD} to V_{SS}	V	
On Resistance (R _{ON})	1			Ωtyp	$V_S = \pm 4.5 \text{ V}, I_S = -10 \text{ mA}$; see Figure 22
	1.2	1.4	1.6	Ω max	$V_{DD} = \pm 4.5 \text{ V}, V_{SS} = \pm 4.5 \text{ V}$
On Resistance Match Between Channels (ΔR _{ON})	0.04			Ωtyp	$V_S = \pm 4.5 \text{ V, } I_S = -10 \text{ mA}$
	0.08	0.09	0.1	Ω max	
On Resistance Flatness (RFLAT(ON))	0.2			Ωtyp	$V_S = \pm 4.5 \text{ V}, I_S = -10 \text{ mA}$
	0.25	0.29	0.34	Ω max	
LEAKAGE CURRENTS					$V_{DD} = +5.5 \text{ V}, V_{SS} = -5.5 \text{ V}$
Source Off Leakage, Is (Off)	±0.1			nA typ	$V_S = \pm 4.5 \text{ V}, V_D = \mp 4.5 \text{ V}; \text{ see Figure 23}$
-	±0.2	±1	±8	nA max	J v v v v v v v v v v v v v v v v v v v
Drain Off Leakage, I _D (Off)	±0.1			nA typ	$V_S = \pm 4.5 \text{ V}, V_D = \mp 4.5 \text{ V}; \text{ see Figure 23}$
5 · · · · · · · · · · · · · · · · · · ·	±0.2	±2	±16	nA max	v ₃ = ± 1.5 v, v _b = 1 1.5 v, see Figure 25
Channel On Leakage, I₀, I₅ (On)	±0.2	<u> </u>	±10	nA typ	$V_S = V_D = \pm 4.5 \text{ V}$; see Figure 24
Charmer On Leakage, 10, 15 (On)	±0.2	±2	±16	nA max	vs = vb = ±4.5 v, see rigure 24
DIGITAL INPUTS	±0.∓	<u> </u>	±10	TIATITIAX	
Input High Voltage, V _{INH}			2.0	V min	
Input Low Voltage, V _{INL}			0.8	V max	
Input Current, Inc or Inh	0.005		0.0	μA typ	$V_{IN} = V_{GND}$ or V_{DD}
Input Current, IINL OF IINH	0.005		±0.1	μΑ typ	VIN — VGND OI VDD
Digital Input Capacitance, C _{IN}	8		±0.1	pF typ	
DYNAMIC CHARACTERISTICS ¹	0			рг тур	
Transition Time, transition	150			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
Transition Time, transition	278	336	376	ns max	$V_s = 2.5 \text{ V}$; see Figure 29
ton (EN)	116	330	370	ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
ton (LIV)	146	166	177	ns max	$V_s = 2.5 \text{ V}$; see Figure 31
t _{OFF} (EN)	186	100	177	ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
torr (LIV)	234	277	310	ns max	$V_S = 2.5 \text{ V}$; see Figure 31
Break-Before-Make Time Delay, t _D	50	2//	310	ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
break before make fille belay, to	30		28.5	ns min	$V_{S1} = V_{S2} = 2.5 \text{ V}$; see Figure 30
Charge Injection	140		20.5	pC typ	$V_S = 0 \text{ V}, R_S = 0 \Omega, C_L = 1 \text{ nF; see Figure 32}$
Off Isolation	70			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$;
Channel-to-Channel Crosstalk	70			dB typ	see Figure 25 $R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 27
Total Harmonic Distortion + Noise (THD + N)	0.007			% typ	R _L = 110 Ω , 5 V p-p, f = 20 Hz to 20 kHz; see Figure 28
–3 dB Bandwidth	15			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 26
C _s (Off)	63			pF typ	$V_s = 0 \text{ V, } f = 1 \text{ MHz}$
C _D (Off)	270			pF typ	$V_s = 0 V, f = 1 MHz$
C _D , C _S (On)	360			pF typ	$V_S = 0 \text{ V, } f = 1 \text{ MHz}$
POWER REQUIREMENTS	1			1 -7 F	$V_{DD} = +5.5 \text{ V}, V_{SS} = -5.5 \text{ V}$
IDD	0.001			μA typ	Digital inputs = 0 V or V_{DD}
V _{DD} /V _{SS}			1.0 ±3.3/±8	μA max V min/max	

 $^{^{\}mbox{\tiny 1}}$ Guaranteed by design, not subject to production test.

12 V SINGLE SUPPLY

 V_{DD} = 12 V \pm 10%, V_{SS} = 0 V, GND = 0 V, unless otherwise noted.

Table 2.

Parameter	25°C	−40°C to +85°C	−40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			$0 V to V_{DD}$	V	
On Resistance (R _{ON})	0.95			Ωtyp	$V_s = 0 \text{ V to } 10 \text{ V}, I_s = -10 \text{ mA}; \text{ see Figure } 22$
	1.1	1.25	1.45	Ω max	$V_{DD} = 10.8 \text{ V}, V_{SS} = 0 \text{ V}$
On Resistance Match Between Channels (ΔR _{ON})	0.03			Ωtyp	$V_S = 10 \text{ V}, I_S = -10 \text{ mA}$
	0.06	0.07	0.08	Ω max	
On Resistance Flatness (R _{FLAT(ON)})	0.2			Ωtyp	$V_S = 0 \text{ V to } 10 \text{ V, } I_S = -10 \text{ mA}$
	0.23	0.27	0.32	Ω max	
LEAKAGE CURRENTS					$V_{DD} = 13.2 \text{ V}, V_{SS} = 0 \text{ V}$
Source Off Leakage, I₅ (Off)	±0.1			nA typ	$V_S = 1 \text{ V}/10 \text{ V}, V_D = 10 \text{ V}/1 \text{ V}; \text{ see Figure 23}$
	±0.2	±1	±8	nA max	
Drain Off Leakage, I _D (Off)	±0.1			nA typ	$V_S = 1 \text{ V}/10 \text{ V}, V_D = 10 \text{ V}/1 \text{ V}; \text{ see Figure 23}$
	±0.2	±2	±16	nA max	
Channel On Leakage, ID, IS (On)	±0.2			nA typ	$V_S = V_D = 1 \text{ V or } 10 \text{ V}$; see Figure 24
	±0.4	±2	±16	nA max	_
DIGITAL INPUTS					
Input High Voltage, V _{INH}			2.0	V min	
Input Low Voltage, V _{INL}			0.8	V max	
Input Current, I _{INL} or I _{INH}	0.001			μA typ	$V_{IN} = V_{GND}$ or V_{DD}
			±0.1	μA max	
Digital Input Capacitance, C _{IN}	8			pF typ	
DYNAMIC CHARACTERISTICS ¹					
Transition Time, ttransition	100			ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
	161	192	220	ns max	$V_S = 8 \text{ V}$; see Figure 29
ton (EN)	80			ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
	95	104	111	ns max	$V_S = 8 \text{ V}$; see Figure 31
t _{OFF} (EN)	144			ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
	173	205	234	ns max	$V_S = 8 \text{ V}$; see Figure 31
Break-Before-Make Time Delay, t _D	25			ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
			18	ns min	$V_{S1} = V_{S2} = 8 \text{ V}$; see Figure 30
Charge Injection	125			pC typ	$V_S = 6 \text{ V}$, $R_S = 0 \Omega$, $C_L = 1 \text{ nF}$; see Figure 32
Off Isolation	70			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 25
Channel-to-Channel Crosstalk	70			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 27
Total Harmonic Distortion + Noise	0.013			% typ	$R_L = 110 \Omega$, 5 V p-p, f = 20 Hz to 20 kHz; see Figure 28
–3 dB Bandwidth	19			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 26
C _s (Off)	60			pF typ	V _S = 6 V, f = 1 MHz
C _D (Off)	270			pF typ	$V_S = 6 \text{ V}, f = 1 \text{ MHz}$
C_D , C_S (On)	350			pF typ	$V_S = 6 V, f = 1 MHz$
POWER REQUIREMENTS					$V_{DD} = 12 \text{ V}$
lod	0.001			μA typ	Digital inputs = 0 V or V _{DD}
			1	μA max	·
lod	230			μA typ	Digital inputs = 5 V
			360	μA max	
V_{DD}			3.3/16	V min/max	

¹ Guaranteed by design, not subject to production test.

5 V SINGLE SUPPLY

 V_{DD} = 5 V \pm 10%, V_{SS} = 0 V, GND = 0 V, unless otherwise noted.

Table 3.

Parameter	25°C	−40°C to +85°C	−40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			$0V$ to V_{DD}	V	
On Resistance (R _{ON})	1.7			Ωtyp	$V_S = 0 \text{ V to } 4.5 \text{ V, } I_S = -10 \text{ mA; see Figure } 22$
	2.15	2.4	2.7	Ω max	$V_{DD} = 4.5 \text{ V}, V_{SS} = 0 \text{ V}$
On Resistance Match Between Channels (ΔR _{ON})	0.05			Ωtyp	$V_S = 0 \text{ V to } 4.5 \text{ V, } I_S = -10 \text{ mA}$
	0.09	0.12	0.15	Ω max	
On Resistance Flatness (R _{FLAT(ON)})	0.4			Ωtyp	$V_S = 0 \text{ V to } 4.5 \text{ V, } I_S = -10 \text{ mA}$
	0.53	0.55	0.6	Ω max	
LEAKAGE CURRENTS					$V_{DD} = 5.5 \text{ V}, V_{SS} = 0 \text{ V}$
Source Off Leakage, Is (Off)	±0.05			nA typ	$V_S = 1 \text{ V}/4.5 \text{ V}, V_D = 4.5 \text{ V}/1 \text{ V}; \text{ see Figure 23}$
	±0.2	±1	±8	nA max	
Drain Off Leakage, ID (Off)	±0.05		_0	nA typ	$V_S = 1 \text{ V}/4.5 \text{ V}, V_D = 4.5 \text{ V}/1 \text{ V}; \text{ see Figure 23}$
2.a 2 22aage, 15 (2)	±0.2	±2	±16	nA max	15 17, 115 1, 15 115 17, 17, 500 11gui e 25
Channel On Leakage, ID, IS (On)	±0.1		0	nA typ	$V_S = V_D = 1 \text{ V or } 4.5 \text{ V; see Figure } 24$
Chamici on Leakage, ib, is (on)	±0.4	±2	±16	nA max	v3 = vb = 1 v or 1.5 v, see rigare 2 r
DIGITAL INPUTS	±0.∓	<u> </u>	±10	TITATION	
Input High Voltage, V _{INH}			2.0	V min	
Input Low Voltage, V _{INL}			0.8	V max	
Input Current, I _{INL} or I _{INH}	0.001		0.0	μA typ	$V_{IN} = V_{GND} \text{ or } V_{DD}$
input current, IINL of IINH	0.001		±0.1	μΑ typ μΑ max	VIN — VGND OI VDD
Digital Input Canaditance C	8		±0.1	•	
Digital Input Capacitance, C _{IN} DYNAMIC CHARACTERISTICS ¹	٥			pF typ	
	175				D 300 0 6 35 75
Transition Time, transition	175	227	200	ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
(FAI)	283	337	380	ns max	$V_S = 2.5 \text{ V}$; see Figure 29
ton (EN)	135	104	212	ns typ	$R_L = 300 \Omega, C_L = 35 pF$
(51)	174	194	212	ns max	$V_S = 2.5 \text{ V}$; see Figure 31
toff (EN)	228	2.42	205	ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	288	342	385	ns max	$V_s = 2.5 \text{ V}$; see Figure 31
Break-Before-Make Time Delay, t _D	30			ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
			21	ns min	$V_{S1} = V_{S2} = 2.5 \text{ V}$; see Figure 30
Charge Injection	70			pC typ	$V_S = 2.5 \text{ V}, R_S = 0 \Omega, C_L = 1 \text{ nF; see Figure 32}$
Off Isolation	70			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$; see Figure 25
Channel-to-Channel Crosstalk	70			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$; see Figure 27
Total Harmonic Distortion + Noise	0.09			% typ	$R_L = 110 \Omega$, $f = 20 Hz$ to $20 kHz$, $V_S = 3.5 V$ p-p; see Figure 28
–3 dB Bandwidth	16			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 26
C _s (Off)	70			pF typ	$V_S = 2.5 \text{ V, } f = 1 \text{ MHz}$
C _D (Off)	300			pF typ	$V_S = 2.5 \text{ V, } f = 1 \text{ MHz}$
C _D , C _S (On)	400			pF typ	$V_S = 2.5 \text{ V, } f = 1 \text{ MHz}$
POWER REQUIREMENTS				15. 57 %	$V_{DD} = 5.5 \text{ V}$
I _{DD}	0.001			μA typ	Digital inputs = 0 V or V_{DD}
	0.001			איייטף	2.3.101 11pats - 0 v 01 vuu
טטו			1	μA max	

 $^{^{\}mbox{\tiny 1}}$ Guaranteed by design, not subject to production test.

3.3 V SINGLE SUPPLY

 V_{DD} = 3.3 V, V_{SS} = 0 V, GND = 0 V, unless otherwise noted.

Table 4.

Parameter	25°C	−40°C to +85°C	−40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			$0VtoV_{DD}$	V	
On Resistance (R _{ON})	3.2	3.4	3.6	Ωtyp	$V_S = 0 \text{ V to V}_{DD}$, $I_S = -10 \text{ mA}$, $V_{DD} = 3.3 \text{ V}$, $V_{SS} = 0 \text{ V}$; see Figure 22
On Resistance Match Between Channels (ΔR _{ON})	0.06	0.07	0.08	Ωtyp	$V_S = 0 \text{ V to } V_{DD}, I_S = -10 \text{ mA}$
On Resistance Flatness (R _{FLAT(ON)})	1.2	1.3	1.4	Ωtyp	$V_S = 0 \text{ V to } V_{DD}, I_S = -10 \text{ mA}$
LEAKAGE CURRENTS					$V_{DD} = 3.6 \text{ V}, V_{SS} = 0 \text{ V}$
Source Off Leakage, Is (Off)	±0.02			nA typ	$V_S = 0.6 \text{ V/3 V}, V_D = 3 \text{ V/0.6 V}; \text{ see Figure 23}$
	±0.25	±1	±8	nA max	
Drain Off Leakage, I _D (Off)	±0.02			nA typ	$V_S = 0.6 \text{ V/3 V}, V_D = 3 \text{ V/0.6 V}; \text{ see Figure 23}$
	±0.25	±2	±16	nA max	
Channel On Leakage, ID, IS (On)	±0.05			nA typ	$V_S = V_D = 0.6 \text{ V or 3 V}$; see Figure 24
	±0.6	±2	±16	nA max	
DIGITAL INPUTS					
Input High Voltage, V _{INH}			2.0	V min	
Input Low Voltage, V _{INL}			0.8	V max	
Input Current, I _{INL} or I _{INH}	0.001			μA typ	$V_{IN} = V_{GND} \text{ or } V_{DD}$
			±0.1	μA max	
Digital Input Capacitance, C _{IN}	8			pF typ	
DYNAMIC CHARACTERISTICS ¹					
Transition Time, trransition	280			ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
	460	526	575	ns max	V _s = 1.5 V; see Figure 29
ton (EN)	227			ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
	308	332	346	ns max	$V_S = 1.5 \text{ V}$; see Figure 31
t _{OFF} (EN)	357			ns typ	$R_L = 300 \Omega, C_L = 35 pF$
	480	549	601	ns max	$V_S = 1.5 \text{ V}$; see Figure 31
Break-Before-Make Time Delay, t _D	25			ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
			20	ns min	$V_{S1} = V_{S2} = 1.5 \text{ V}$; see Figure 30
Charge Injection	60			pC typ	$V_S = 1.5 \text{ V}, R_S = 0 \Omega, C_L = 1 \text{ nF; see Figure 32}$
Off Isolation	70			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$; see Figure 25
Channel-to-Channel Crosstalk	70			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$; see Figure 27
Total Harmonic Distortion + Noise	0.15			% typ	$R_L = 110 \Omega$, $f = 20 Hz$ to $20 kHz$, $V_S = 2 V p-p$; see Figure 28
−3 dB Bandwidth	15			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 26
C _s (Off)	76			pF typ	V _S = 1.5 V, f = 1 MHz
C _D (Off)	316			pF typ	$V_S = 1.5 \text{ V, } f = 1 \text{ MHz}$
C_D , C_S (On)	420			pF typ	$V_S = 1.5 V, f = 1 MHz$
POWER REQUIREMENTS					$V_{DD} = 3.6 \text{ V}$
I _{DD}	0.001			μA typ	Digital inputs = 0 V or V _{DD}
		1.0	1.0	μA max	
V_{DD}			3.3/16	V min/max	

 $^{^{\}mbox{\tiny 1}}$ Guaranteed by design, not subject to production test.

CONTINUOUS CURRENT PER CHANNEL, S OR D

Table 5.

Parameter	25°C	85°C	125°C	Unit
CONTINUOUS CURRENT, S OR D				
$V_{DD} = +5 \text{ V}, V_{SS} = -5 \text{ V}$				
TSSOP ($\theta_{JA} = 150.4$ °C/W)	315	189	95	mA maximum
LFCSP ($\theta_{JA} = 48.7^{\circ}$ C/W)	504	259	112	mA maximum
$V_{DD} = 12 \text{ V}, V_{SS} = 0 \text{ V}$				
TSSOP ($\theta_{JA} = 150.4$ °C/W)	378	221	112	mA maximum
LFCSP ($\theta_{JA} = 48.7^{\circ}$ C/W)	627	311	126	mA maximum
$V_{DD} = 5 \text{ V}, V_{SS} = 0 \text{ V}$				
TSSOP ($\theta_{JA} = 150.4$ °C/W)	249	158	91	mA maximum
LFCSP ($\theta_{JA} = 48.7^{\circ}$ C/W)	403	224	105	mA maximum
$V_{DD} = 3.3 \text{ V}, V_{SS} = 0 \text{ V}$				
TSSOP ($\theta_{JA} = 150.4$ °C/W)	256	165	98	mA maximum
LFCSP ($\theta_{JA} = 48.7^{\circ}$ C/W)	410	235	116	mA maximum

ABSOLUTE MAXIMUM RATINGS

 $T_A = 25$ °C, unless otherwise noted.

Table 6.

Parameter	Rating
V _{DD} to V _{SS}	18 V
V_{DD} to GND	−0.3 V to +18 V
V _{ss} to GND	+0.3 V to -18 V
Analog Inputs ¹	$V_{SS} - 0.3 \text{ V to } V_{DD} + 0.3 \text{ V or}$ 30 mA, whichever occurs first
Digital Inputs ¹	GND $- 0.3 \text{ V}$ to $\text{V}_{DD} + 0.3 \text{ V}$ or 30 mA, whichever occurs first
Peak Current, S or D	1150 mA (pulsed at 1 ms, 10% duty-cycle maximum)
Continuous Current, S or D ²	Data + 15%
Operating Temperature Range	
Industrial (Y Version)	−40°C to +125°C
Storage Temperature Range	−65°C to +150°C
Junction Temperature	150°C
16-Lead TSSOP, θ _{JA} Thermal Impedance (2-Layer Board)	150.4°C/W
16-Lead LFCSP, θ _{JA} Thermal Impedance (4-Layer Board)	48.7°C/W
Reflow Soldering Peak Temperature, Pb free	260°C

¹ Overvoltages at IN, S, or D are clamped by internal diodes. Current should be limited to the maximum ratings given.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

² See Table 5.

PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS

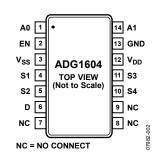


Figure 2. 14-Lead TSSOP Pin Configuration

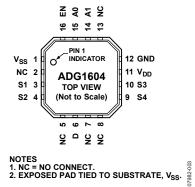


Figure 3. 16-Lead LFCSP Pin Configuration

Table 7. Pin Function Descriptions

Pin No.			
14-Lead TSSOP	16-Lead LFCSP	Mnemonic	Description
1	15	A0	Logic Control Input.
2	16	EN	Active High Digital Input. When this pin is low, the device is disabled and all switches are off. When this pin is high, the Ax logic inputs determine the on switch.
3	1	V _{SS}	Most Negative Power Supply Potential.
4	3	S1	Source Terminal. This pin can be an input or output.
5	4	S2	Source Terminal. This pin can be an input or output.
6	6	D	Drain Terminal. This pin can be an input or output.
7, 8, 9	2, 5, 7, 8, 13	NC	No Connection.
10	9	S4	Source Terminal. This pin can be an input or output.
11	10	S3	Source Terminal. This pin can be an input or output.
12	11	V_{DD}	Most Positive Power Supply Potential.
13	12	GND	Ground (0 V) Reference.
14	14	A1	Logic Control Input.
N/A	17 (EPAD)	EP (EPAD)	Exposed Pad. Tied to substrate, Vss.

Table 8. ADG1604 Truth Table

EN	A1	A0	S 1	S2	S3	S4
0	Х	Х	Off	Off	Off	Off
1	0	0	On	Off	Off	Off
1	0	1	Off	On	Off	Off
1	1	0	Off	Off	On	Off
_ 1	1	1	Off	Off	Off	On

TYPICAL PERFORMANCE CHARACTERISTICS

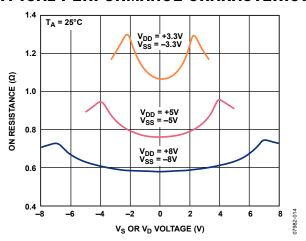


Figure 4. On Resistance as a Function of V_D (V_S) for Dual Supply

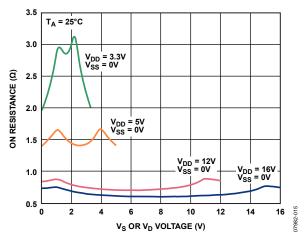


Figure 5. On Resistance as a Function of V_D (V_S) for Single Supply

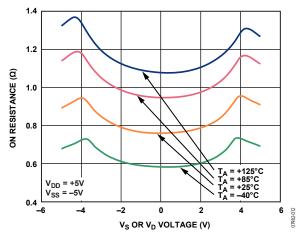


Figure 6. On Resistance as a Function of V_D (V_S) for Different Temperatures, ± 5 V Dual Supply

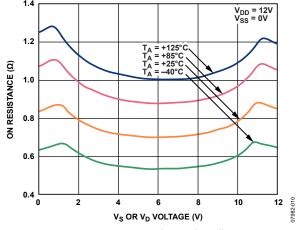


Figure 7. On Resistance as a Function of V_D (V_S) for Different Temperatures, 12 V Single Supply

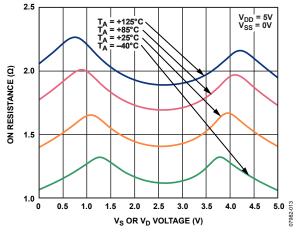


Figure 8. On Resistance as a Function of V_D (V_S) for Different Temperatures, 5 V Single Supply

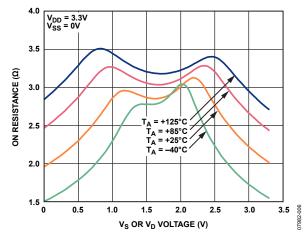


Figure 9. On Resistance as a Function of V_D (V_S) for Different Temperatures, 3.3 V Single Supply

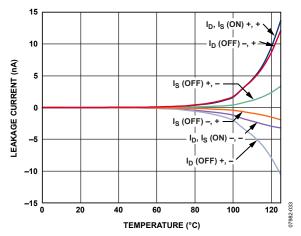


Figure 10. Leakage Currents as a Function of Temperature, ± 5 V Dual Supply

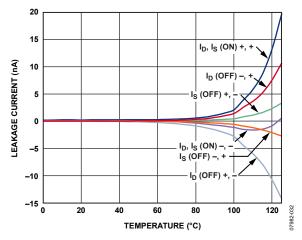


Figure 11. Leakage Currents as a Function of Temperature, 12 V Single Supply

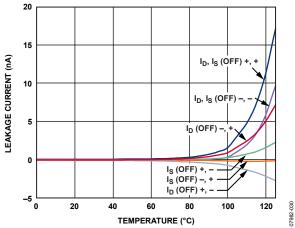


Figure 12. Leakage Currents as a Function of Temperature, 5 V Single Supply

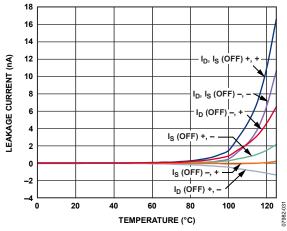


Figure 13. Leakage Currents as a Function of Temperature, 3.3 V Single Supply

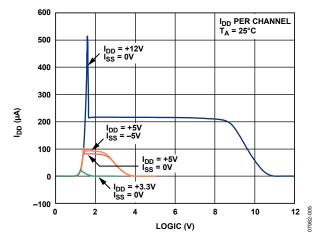


Figure 14. IDD vs. Logic Level

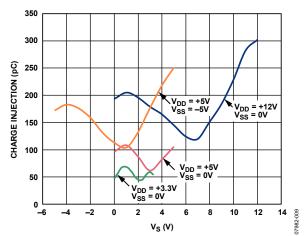


Figure 15. Charge Injection vs. Source Voltage

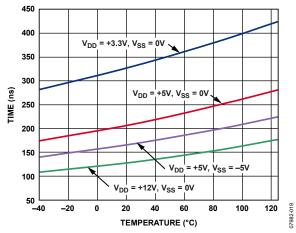


Figure 16. ton/toff Times vs. Temperature

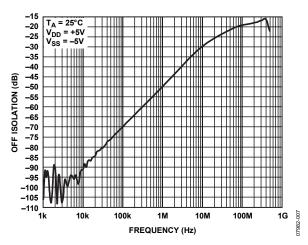


Figure 17. Off Isolation vs. Frequency

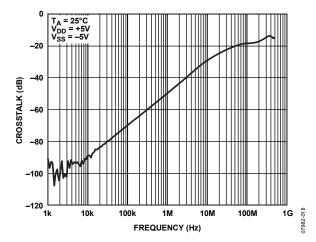


Figure 18. Crosstalk vs. Frequency

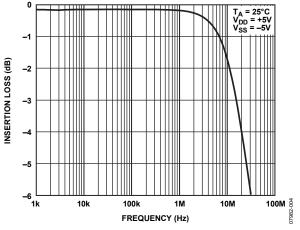


Figure 19. On Response vs. Frequency

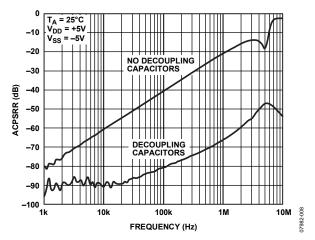


Figure 20. ACPSRR vs. Frequency

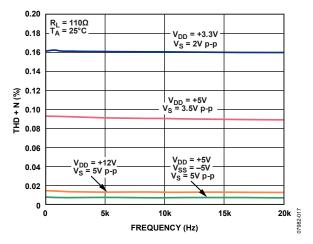
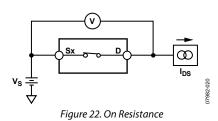
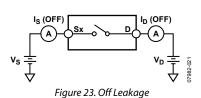
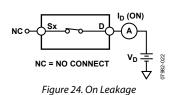


Figure 21. THD + N vs. Frequency

TEST CIRCUITS







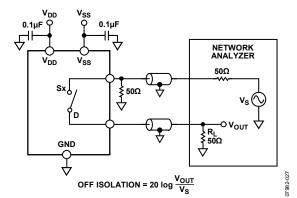


Figure 25. Off Isolation

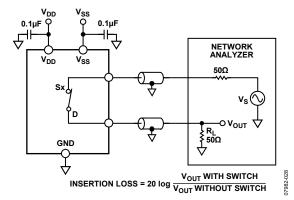


Figure 26. Bandwidth

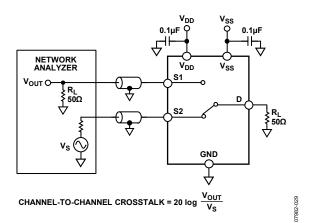


Figure 27. Channel-to-Channel Crosstalk

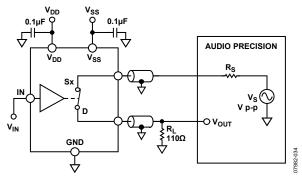


Figure 28. THD + Noise

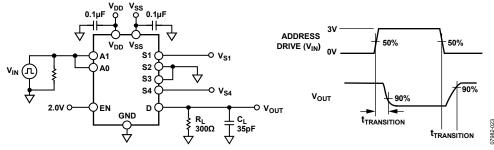
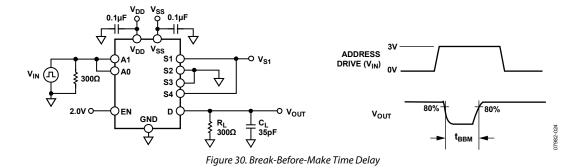


Figure 29. Address to Output Switching Times



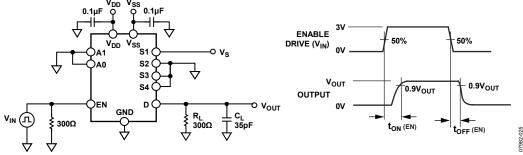


Figure 31. Enable-to-Output Switching Delay

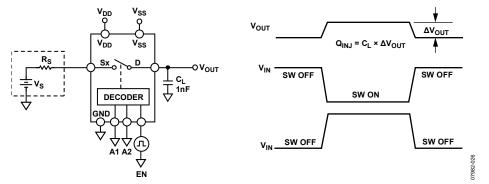


Figure 32. Charge Injection

TERMINOLOGY

 I_{DD}

The positive supply current.

 I_{ss}

The negative supply current.

 $V_D(V_S)$

The analog voltage on Terminal D and Terminal S.

Ron

The ohmic resistance between Terminal D and Terminal S.

R_{FLAT(ON)}

Flatness that is defined as the difference between the maximum and minimum value of on resistance measured over the specified analog signal range.

Is (Off)

The source leakage current with the switch off.

I_D (Off)

The drain leakage current with the switch off.

 $I_D, I_S(On)$

The channel leakage current with the switch on.

 V_{INI}

The maximum input voltage for Logic 0.

 V_{INH}

The minimum input voltage for Logic 1.

IINL (IINH)

The input current of the digital input.

Cs (Off)

The off switch source capacitance, which is measured with reference to ground.

CD (Off)

The off switch drain capacitance, which is measured with reference to ground.

 C_D , C_S (On)

The on switch capacitance, which is measured with reference to ground.

 C_{IN}

The digital input capacitance.

tTRANSITION

The delay time between the 50% and 90% points of the digital input and switch on condition when switching from one address state to another. See Figure 29.

ton (EN)

The delay between applying the digital control input and the output switching on. See Figure 31.

toff (EN)

The delay between applying the digital control input and the output switching off. See Figure 31.

Charge Injection

A measure of the glitch impulse transferred from the digital input to the analog output during switching. See Figure 32.

Off Isolation

A measure of unwanted signal coupling through an off switch. See Figure 25.

Crosstalk

A measure of unwanted signal that is coupled through from one channel to another as a result of parasitic capacitance. See Figure 27.

Bandwidth

The frequency at which the output is attenuated by 3 dB. See Figure 26.

On Response

The frequency response of the on switch.

Insertion Loss

The loss due to the on resistance of the switch.

Total Harmonic Distorition + Noise (THD + N)

The ratio of the harmonic amplitude plus noise of the signal to the fundamental. See Figure 28.

AC Power Supply Rejection Ratio (ACPSRR)

The ratio of the amplitude of signal on the output to the amplitude of the modulation. This is a measure of the ability of the part to avoid coupling noise and spurious signals that appear on the supply voltage pin to the output of the switch. The dc voltage on the device is modulated by a sine wave of 0.62 V p-p.

OUTLINE DIMENSIONS

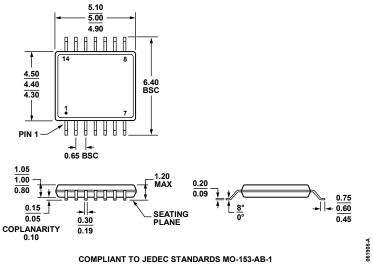


Figure 33. 14-Lead Thin Shrink Small Outline Package [TSSOP] (RU-14) Dimensions shown in millimeters

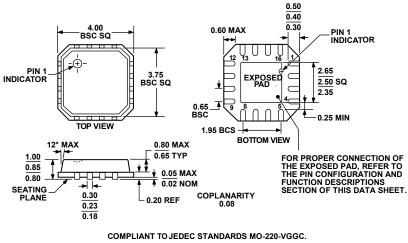


Figure 34. 16-Lead Lead Frame Chip Scale Package [LFCSP_VQ] 4 mm × 4 mm Body, Very Thin Quad (CP-16-13) Dimensions shown in millimeters

ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option
ADG1604BRUZ ¹	−40°C to +125°C	14-Lead Thin Shrink Small Outline Package [TSSOP]	RU-14
ADG1604BRUZ-REEL ¹	-40°C to +125°C	14-Lead Thin Shrink Small Outline Package [TSSOP]	RU-14
ADG1604BRUZ-REEL71	-40°C to +125°C	14-Lead Thin Shrink Small Outline Package [TSSOP]	RU-14
ADG1604BCPZ- REEL ¹	-40°C to +125°C	16-Lead Lead Frame Chip Scale Package [LFCSP_VQ]	CP-16-13
ADG1604BCPZ-REEL7 ¹	-40°C to +125°C	16-Lead Lead Frame Chip Scale Package [LFCSP_VQ]	CP-16-13

¹ Z = RoHS Compliant Part.

NOTES

NOTES

NOTES